

SavantIC Semiconductor

Product Specification

Silicon PNP Power Transistors

2N6285 2N6286 2N6287

DESCRIPTION

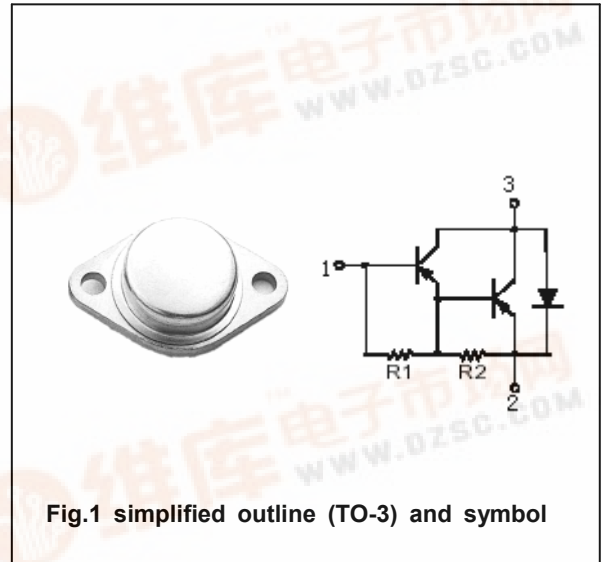
- With TO-3 package
- Complement to type 2N6282/6283/6284
- High DC current gain
- DARLINGTON

APPLICATIONS

- For use in general-purpose amplifier and low-frequency switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6285	Open emitter	-60	V
		2N6286		-80	
		2N6287		-100	
V_{CEO}	Collector-emitter voltage	2N6285	Open base	-60	V
		2N6286		-80	
		2N6287		-100	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-20	A
I_{CM}	Collector current-peak			-40	A
I_B	Base current			-0.5	A
P_D	Total Power Dissipation		$T_C = 25\square$	160	W
T_j	Junction temperature			200	$\square$
T_{stg}	Storage temperature			-65~200	$\square$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	1.09	$\square/W$

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CHARACTERISTICS

T_j=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	2N6285	I _C =-0.2A ; I _B =0	-60			V
		2N6286		-80			
		2N6287		-100			
V _{CEsat-1}	Collector-emitter saturation voltage		I _C =-10A; I _B =-40mA			-2.0	V
V _{CEsat-2}	Collector-emitter saturation voltage		I _C =-20A ; I _B =-200mA			-3.0	V
V _{BEsat}	Base-emitter saturation voltage		I _C =-20A ; I _B =-200mA			-4.0	V
V _{BE}	Base-emitter on voltage		I _C =-10A ; V _{CE} =-3V			-2.8	V
I _{CEO}	Collector cut-off current	2N6285	V _{CE} =-30V; I _B =0			-1.0	mA
		2N6286	V _{CE} =-40V; I _B =0				
		2N6287	V _{CE} =-50V; I _B =0				
I _{CEX}	Collector cut-off current	2N6285	V _{CE} =-60V; V _{BE} =-1.5V T _C =150℃			-0.5 -5.0	mA
		2N6286	V _{CE} =-80V; V _{BE} =-1.5V T _C =150℃			-0.5 -5.0	
		2N6287	V _{CE} =-100V; V _{BE} =-1.5V T _C =150℃			-0.5 -5.0	
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-2.0	mA
h _{FE-1}	DC current gain		I _C =-10A ; V _{CE} =-3V	750		18000	
h _{FE-2}	DC current gain		I _C =-20A ; V _{CE} =-3V	100			
C _{OB}	Output capacitance		I _E =0; V _{CB} =-10V; f=1MHz			600	pF

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PACKAGE OUTLINE

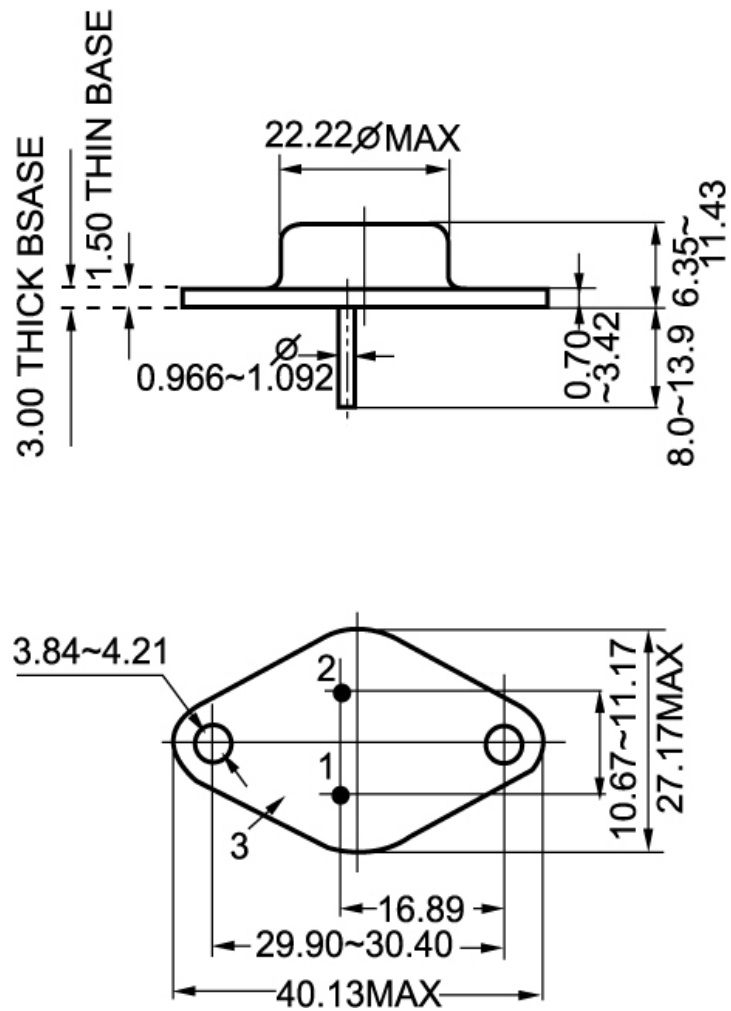


Fig.2 outline dimensions (unindicated tolerance:±0.10mm)